

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|---|---|------------------|---------|------------------|
| L1 | 8 | ("20030030153" "5734200" "6251694" "6737745").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 12:48 |
| L2 | 14577 | copper with pad | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L3 | 137 | L2 with window | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L4 | 68 | L3 and wire | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L5 | 3458 | copper with pad and barrier | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L6 | 1269 | L5 and barrier with pad | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L7 | 1269 | L6 and barrier with pad | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L8 | 180 | L6 and window | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L9 | 119 | L8 and wire | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |

| | | | | | | |
|-----|------|--|---|----|----|------------------|
| L10 | 118 | L9 and (IC integrated adj circuit die wafer semiconductor silioecn chip) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L11 | 0 | passivation with spin adj on adj process | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L12 | 57 | passivation with spin near2 process | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L13 | 61 | passivation with spin with pad | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L14 | 141 | passivation with spin and pad with passivation and wire | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L15 | 103 | L14 not L13 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L16 | 740 | advantages with spin near2 coat\$3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L17 | 2 | advantages with spin near2 coat\$3 | USOCR | OR | ON | 2006/01/21 13:32 |
| L18 | 232 | advantages with spin near2 coat\$3 | USPAT | OR | ON | 2006/01/21 13:32 |
| L19 | 58 | L18 and wire | USPAT | OR | ON | 2006/01/21 13:32 |
| L20 | 0 | "20050208701".pn. | USPAT | OR | ON | 2006/01/21 13:32 |
| L21 | 1 | "20050208701".pn. | US-PGPUB | OR | ON | 2006/01/21 13:32 |
| L22 | 5643 | annealing with oxide indium with bismuth | US-PGPUB | OR | ON | 2006/01/21 13:32 |
| L23 | 3949 | annealing with oxide indium near bismuth | US-PGPUB | OR | ON | 2006/01/21 13:32 |
| L24 | 0 | annealing with oxide with indium near3 bismuth | US-PGPUB | OR | ON | 2006/01/21 13:32 |

| | | | | | | |
|-----|---|--|---|----|-----|------------------|
| L25 | 1 | annealing with oxide with indium near3 bismuth | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L26 | 1 | anneal\$5 with oxide with indium near3 bismuth | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L27 | 9 | anneal\$5 with oxide with(In adj bi) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L28 | 9 | anneal\$5 with oxid\$3 with(In adj bi) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L29 | 0 | oxid\$3 with(In adj bi)same protection with oxide | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L30 | 5 | oxid\$3 with(In adj bi)same protect\$3 with oxide | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L31 | 2 | "20030197258".pn. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L32 | 0 | ("5685968.pn.").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/01/21 13:32 |
| L33 | 2 | "5685968".pn. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |

| | | | | | | |
|-----|------|--|---|----|----|------------------|
| L34 | 1 | L33 and defect | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 13:32 |
| L35 | 3917 | (metallization pad contact wiring film layer) with (copper cu) and (overcoat coat passivation solder near2 resist patternable near2 material) and barrier and (window hole aperture opening) | US-PGPUB | OR | ON | 2006/01/21 14:39 |
| L36 | 137 | ((metallization pad contact wiring film layer) and (copper cu) and (overcoat coat passivation solder near2 resist patternable near2 material) and barrier and (window hole aperture opening)).clm. | US-PGPUB | OR | ON | 2006/01/21 14:39 |
| L37 | 137 | ((metallization pad contact wiring film layer) and (copper cu) and (overcoat coat passivation solder near2 resist patternable near2 material) and barrier and (window hole aperture opening)).clm. | US-PGPUB | OR | ON | 2006/01/21 14:39 |